

**MULTI-BIT PHASE CHANGE MEMORY CELL AND MULTI-BIT PHASE
CHANGE MEMORY INCLUDING THE SAME, METHOD OF FORMING A
MULTI-BIT PHASE CHANGE MEMORY, AND METHOD OF PROGRAMMING A
MULTI-BIT PHASE CHANGE MEMORY**

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ABSTRACT OF THE DISCLOSURE

A multi-bit phase change memory cell including a stack
of a plurality of conductive layers and a plurality of phase
change material layers, each of the phase change material
10 layers disposed between a corresponding pair of conductive
layers and having electrical resistances that are different
from one another.